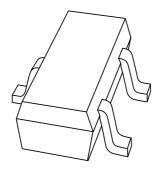
DISCRETE SEMICONDUCTORS

DATA SHEET



BAV70THigh-speed double diode

Product specification Supersedes data of 1997 Dec 19 2004 Feb 04





High-speed double diode

BAV70T

FEATURES

- · Very small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 100V
- Repetitive peak reverse voltage: max. 100 V
- Repetitive peak forward current: max. 500 mA.

APPLICATIONS

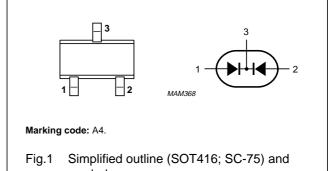
• High-speed switching in e.g. surface mounted circuits.

DESCRIPTION

Two high-speed switching diodes in a common cathode configuration, fabricated in planar technology, in a very small rectangular SMD SOT416 (SC-75) package.

PINNING

PIN	DESCRIPTION	
1	anode 1	
2	anode 2	
3	common cathode	



symbol.

ORDERING INFORMATION

TYPE	PACKAGE			
NUMBER	NAME	DESCRIPTION	VERSION	
BAV70T	_	plastic surface mounted package; 3 leads SOT4		

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode (unless otherwise specified)					
V _{RRM}	repetitive peak reverse voltage		_	100	V
V _R	continuous reverse voltage		_	100	V
I _F	continuous forward current	T _s = 90 °C; see Fig.2			
		single diode loaded	_	150	mA
		both diodes loaded	_	75	mA
I _{FRM}	repetitive peak forward current		_	500	mA
I _{FSM}	non-repetitive peak forward current	square wave; T _j = 25 °C prior to surge; see Fig.4			
		t = 1 μs	_	4	Α
		t = 1 ms	_	1	Α
		t = 1 s	_	0.5	Α
P _{tot}	total power dissipation	T _s = 90 °C; one diode loaded	_	170	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	+150	°C

2004 Feb 04 2

High-speed double diode

BAV70T

CHARACTERISTICS

 T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT	
Per diode					
V _F	forward voltage	see Fig.3			
		I _F = 1 mA	0.715	V	
		I _F = 10 mA	0.855	V	
		I _F = 50 mA	1	V	
		I _F = 150 mA	1.25	V	
I _R	reverse current	see Fig.5			
		V _R = 25 V	30	nA	
		V _R = 75 V	2	μΑ	
		$V_R = 25 \text{ V}; T_j = 150 ^{\circ}\text{C}$	60	μΑ	
		V _R = 75 V; T _j = 150 °C	100	μΑ	
C _d	diode capacitance	V _R = 0; f = 1 MHz; see Fig.6	1.5	pF	
t _{rr}	reverse recovery time	switching from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA; see Fig.7	4	ns	
V _{fr}	forward recovery voltage	switched to $I_F = 10 \text{ mA}$; $t_r = 20 \text{ ns}$; see Fig.8	1.75	V	

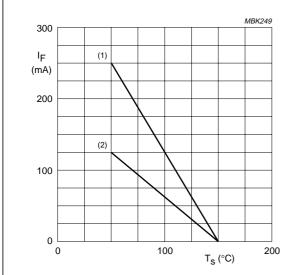
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-s)}	thermal resistance from junction to soldering point	one diode loaded	350	K/W

High-speed double diode

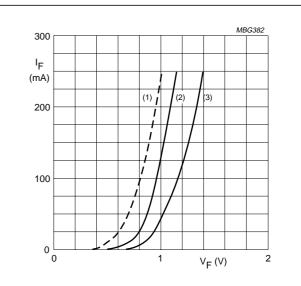
BAV70T

GRAPHICAL DATA



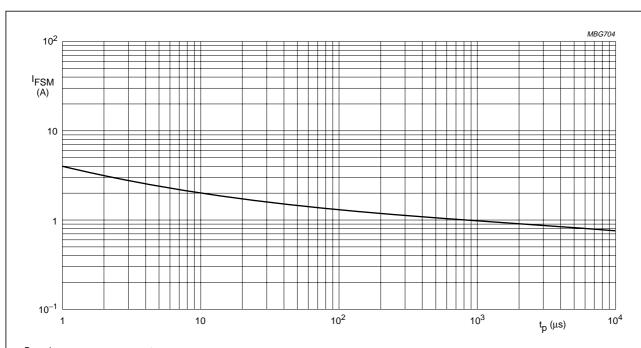
- (1) One diode loaded.
- (2) Both diodes loaded.

Fig.2 Maximum permissible continuous forward current per diode as a function of soldering point temperature.



- (1) T_i = 150 °C; typical values.
- (2) T_i = 25 °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage.

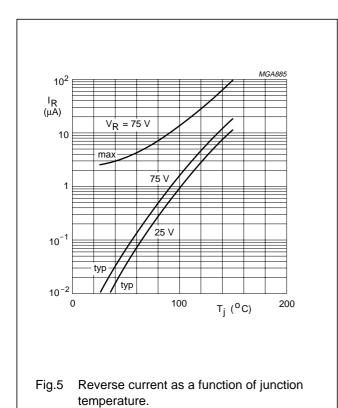


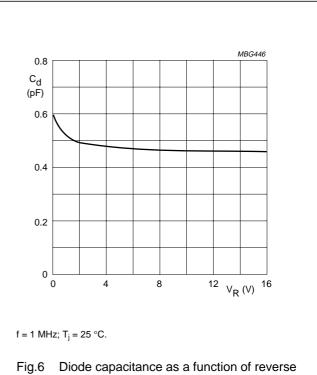
Based on square wave currents. $T_i = 25$ °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

High-speed double diode

BAV70T



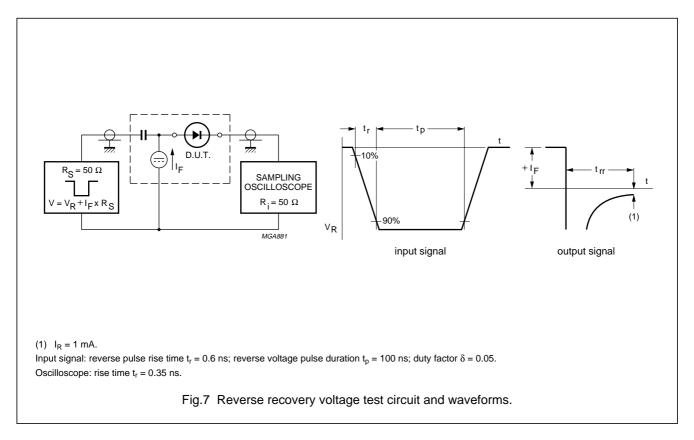


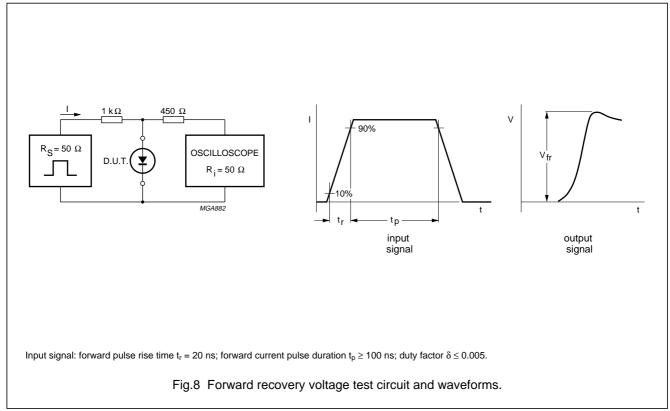
voltage; typical values.

2004 Feb 04 5

High-speed double diode

BAV70T





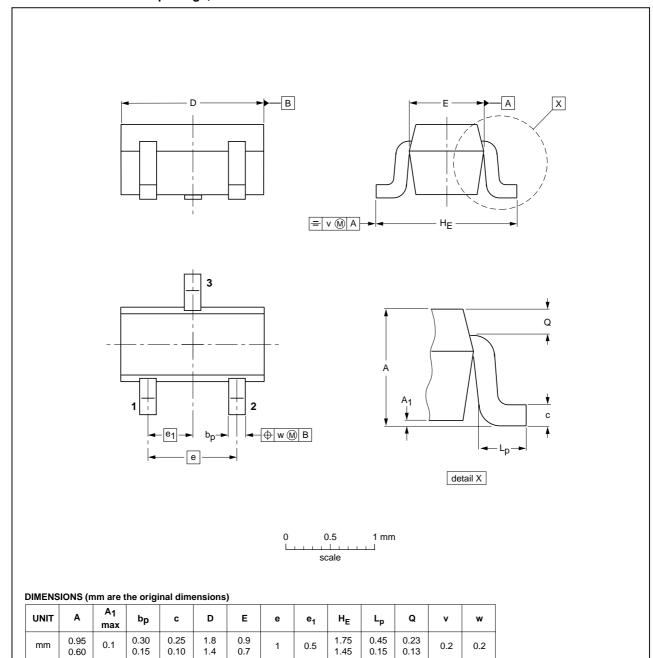
High-speed double diode

BAV70T

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT416



	NE REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT416			SC-75			97-02-28

High-speed double diode

BAV70T

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

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- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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SCA76

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